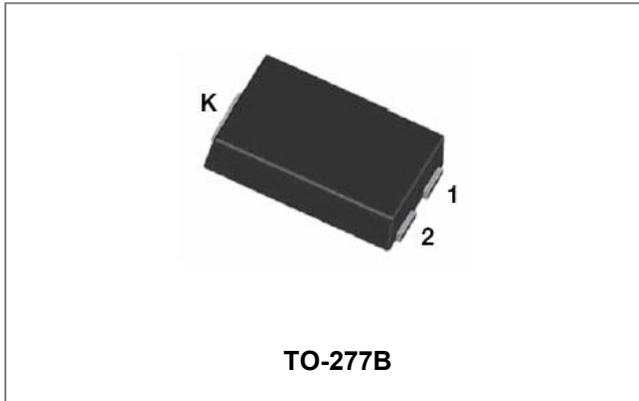


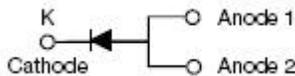
ST2080S SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- “-A” is an AEC-Q101 qualified device
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	80	V
Working Peak Reverse Voltage	V _{RWM}			
DC Blocking Voltage	V _R			
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _L =115°C, rectangular wave form	20	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse, T _c = 25 °C	150	A

Electrical Characteristics:

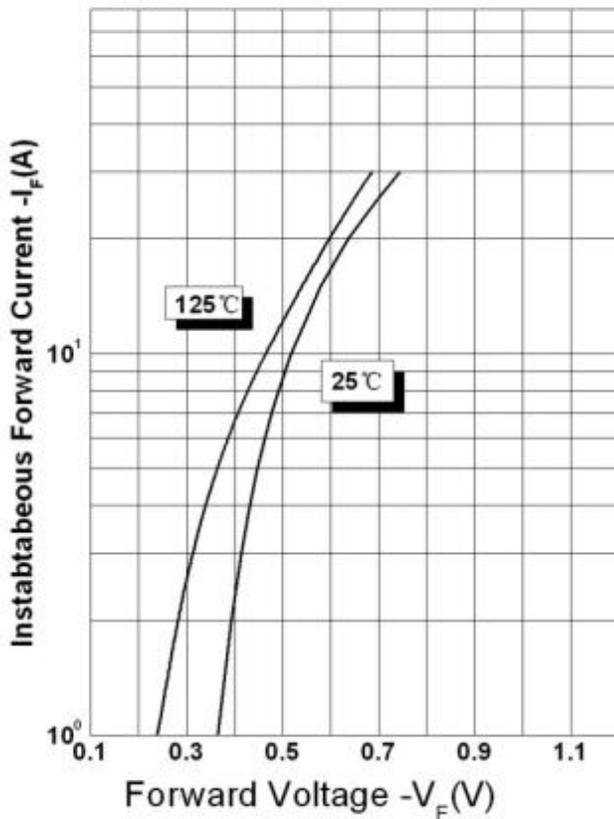
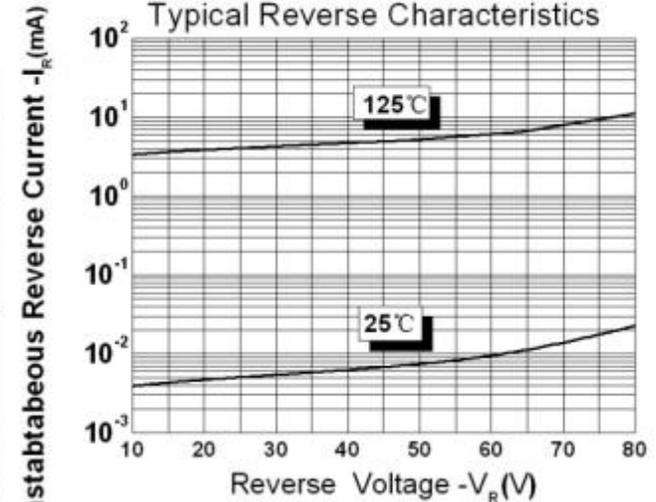
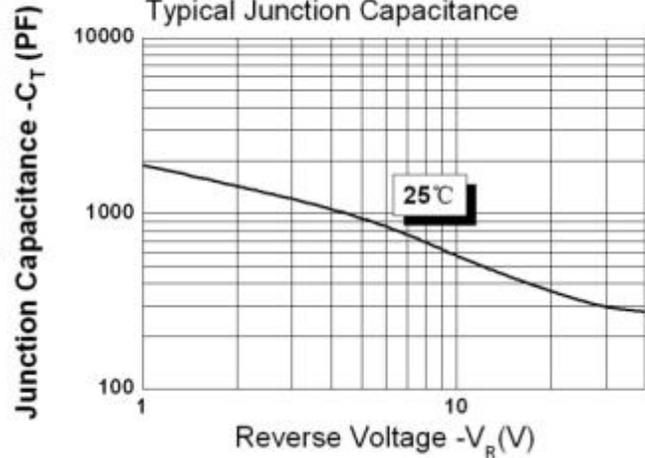
Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 10A, Pulse, T _J = 25 °C	0.52	-	V
		@ 20A, Pulse, T _J = 25 °C	0.64	0.70	
	V _{F2}	@ 10A, Pulse, T _J = 125 °C	0.46	-	V
		@ 20A, Pulse, T _J = 125 °C	0.60	0.65	
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	22	300	uA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	11	75	mA
Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	900	-	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

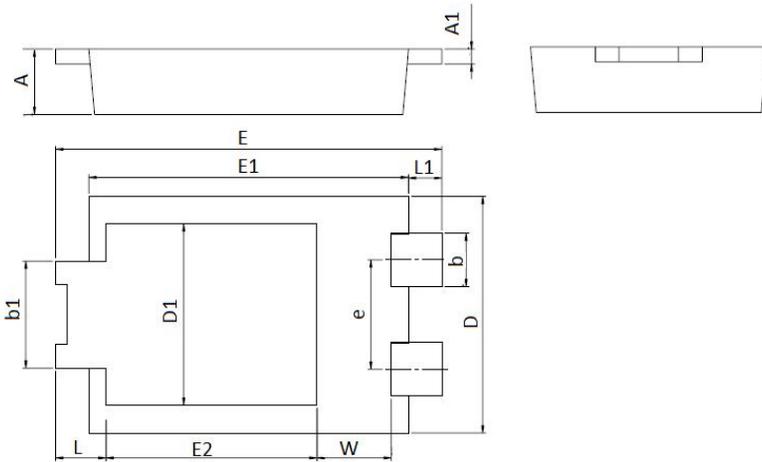
* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

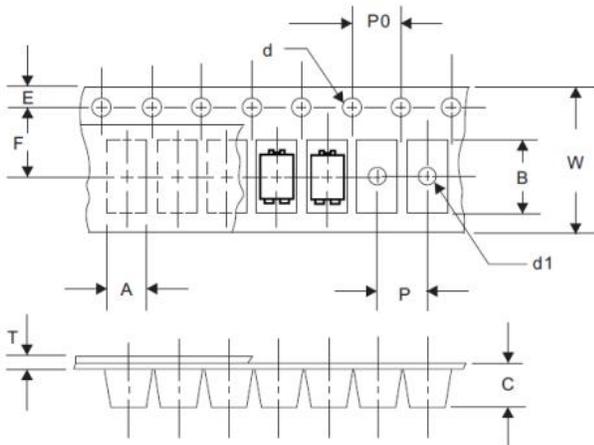
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta\text{JA}}$	DC operation	72(Note1) 30(Note2)	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	0.08	g

NOTE: 1. FR-4 PCB, 2 oz Copper. Minimum recommended pad layout
 2. Polyimide PCB, 2 oz Copper. Cathode pad dimensions 18.8x14.4mm , Anode pad dimensions 5.6x14.4mm

Ratings and Characteristics Curves
Figure 1
Typical Forward Characteristics

Figure 2
Typical Reverse Characteristics

Figure 3
Typical Junction Capacitance


Mechanical Dimensions TO-277B


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.95	1.25	0.037	0.049
A1	0.20	0.30	0.008	0.012
b	0.85	0.95	0.033	0.037
b1	1.70	1.90	0.067	0.075
D	3.88	4.08	0.153	0.161
D1	2.90	3.20	0.114	0.126
e	1.74	1.94	0.069	0.076
E	6.30	6.70	0.248	0.264
E1	5.28	5.48	0.208	0.216
E2	3.40	3.70	0.134	0.146
L	0.70	1.00	0.028	0.039
L1	0.41	0.71	0.016	0.028
W	1.10	1.40	0.043	0.055

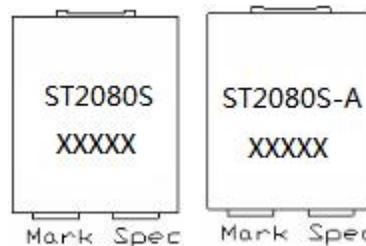
Carrier Tape Specification TO-277B


SYMBOL	Millimeters	
	Min.	Max.
A	4.28	4.48
B	6.80	7.10
C	1.30	1.50
d	1.40	1.60
d1	-	1.50
E	1.65	1.85
F	5.40	5.60
P	7.90	8.10
P0	3.90	4.10
T	0.24	0.44
W	11.70	12.30

Ordering Information

Device	Package	Shipping
ST2080S	TO-277B(Pb-Free)	5000pcs/ reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram


Where XXXXX is YYWWL

ST = Device Type
 20 = Forward Current (20A)
 80 = Reverse Voltage (80V)
 S = Package type
 -A = AEC-Q101
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

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